

# isc Silicon NPN Power Transistor

### **DESCRIPTION**

- Good Linearity of hFE
- High Collector Current
- · Wide Area of Safe Operation
- · High Reliability
- Complement to Type 2SB757
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### **APPLICATIONS**

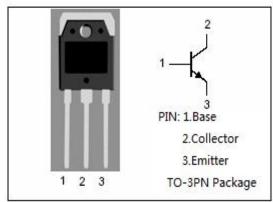
- · Audio amplifier applications
- Series regulators applications
- General purpose power amplifiers

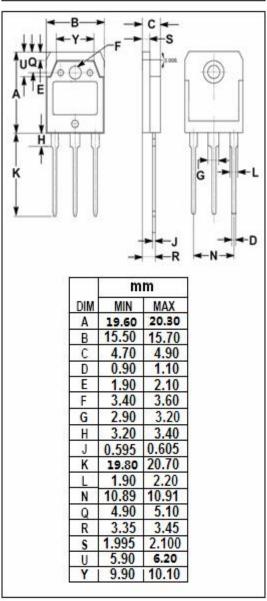
# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	V	
VCEO	Collector-Emitter Voltage	40	V
$V_{EBO}$	Emitter-Base voltage	5	V
Ic	Collector Current-Continuous 15		Α
lв	Base Current-Continuous	5	Α
Pc	Collector Power Dissipation @ T <sub>C</sub> =25°C  80		W
Тл	Junction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
Rth j-c	Thermal Resistance,Junction to Case		°C/W







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2SD847

### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	40			V			
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 0.1mA ; I <sub>E</sub> = 0	40			V			
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 0.1mA ; I <sub>C</sub> = 0	5			V			
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			0.8	V			
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 5A; I <sub>B</sub> = 0.5A			1.8	V			
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 40V ; I <sub>E</sub> = 0			0.01	mA			
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA			
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 5A ; V <sub>CE</sub> = 2V	40		240				
Switching times									
ton	Turn-on Time				1.0	μs			
t <sub>stg</sub>	Storage Time	l <sub>C</sub> = 15A , l <sub>B1</sub> = l <sub>B2</sub> = 1.5A R <sub>L</sub> = 2 Ω ;P <sub>W</sub> =20 μ s Duty Cycle≤2%			2.0	μS			
t <sub>f</sub>	Fall Time	Duty Cycle < 2 /0			1.0	μ <b>S</b>			

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